

Supporting Information

Low-cost and high-performance selenium indoor photovoltaics

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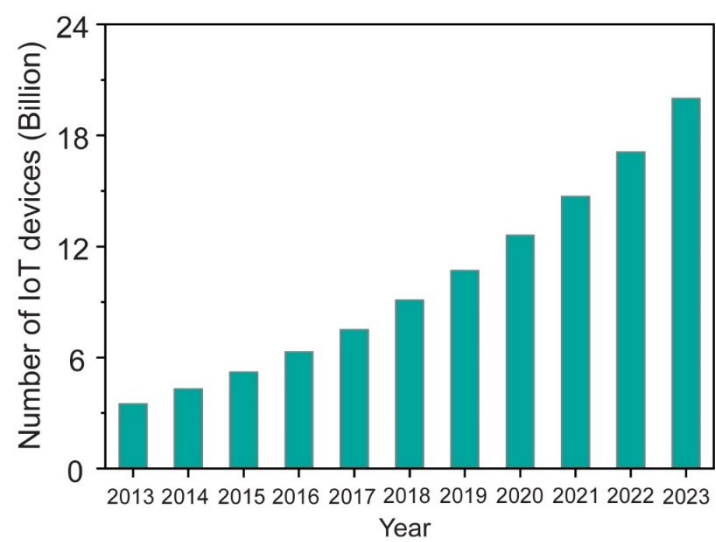


Fig. S1. Number of IoT device connections.¹

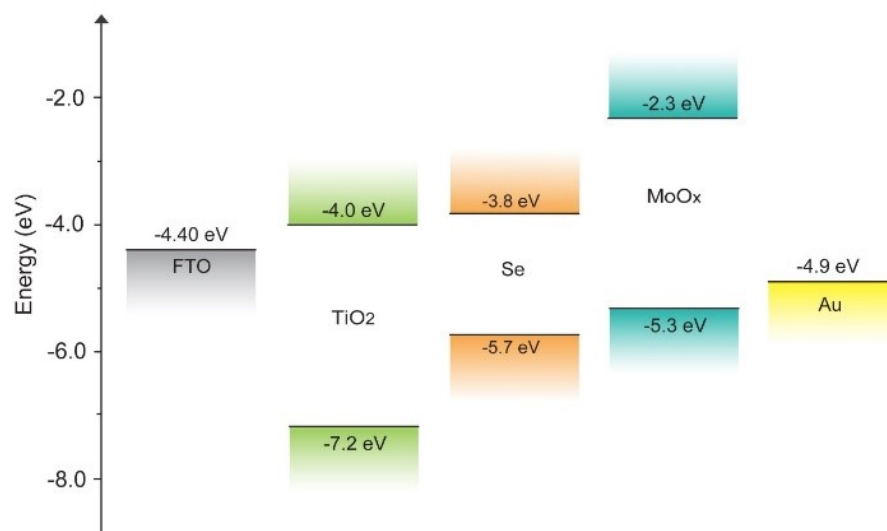


Fig. S2. The schematic energy level diagram of the Se solar cell device.^{2,3}

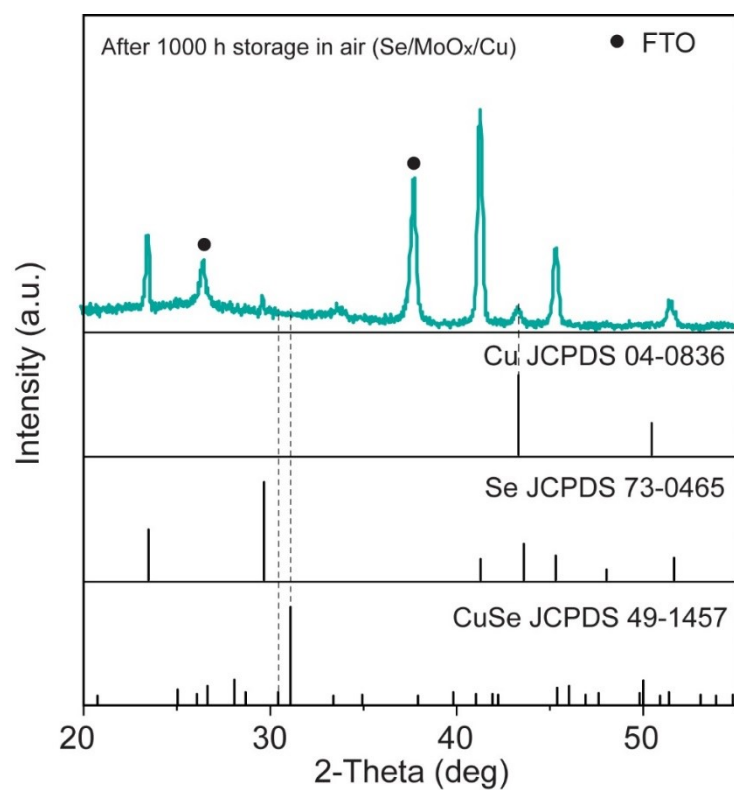


Fig. S3. XRD pattern of Se/MoO_x/Cu device stored in ambient atmosphere at room temperature for 1000 h.

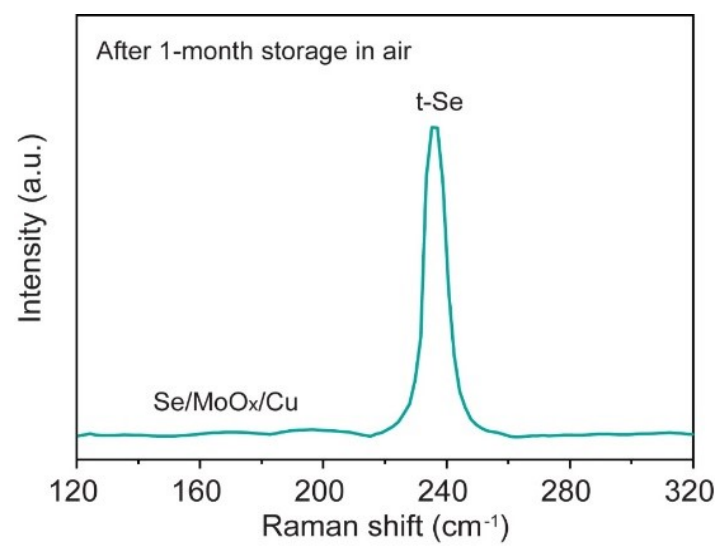


Fig. S4. Raman spectrum of Se/MoO_x/Cu device after 1-month storage in air.

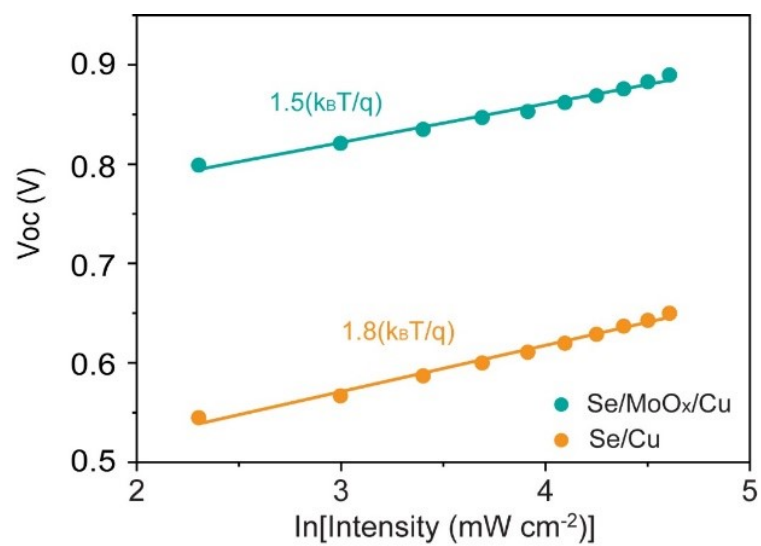


Fig. S5. V_{oc} -light intensity dependence of Se/Cu and Se/MoO_x/Cu devices.

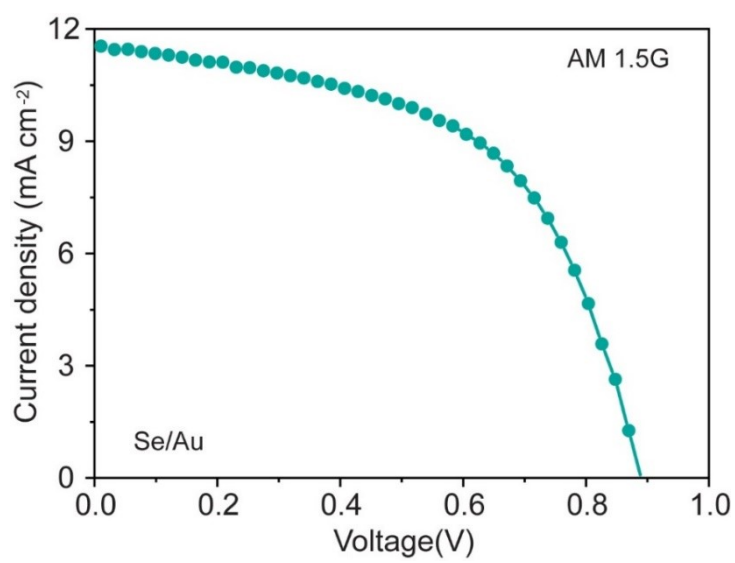


Fig. S6. J-V curve of Se/Au device under standard one-sun illumination (100 mW cm⁻²).

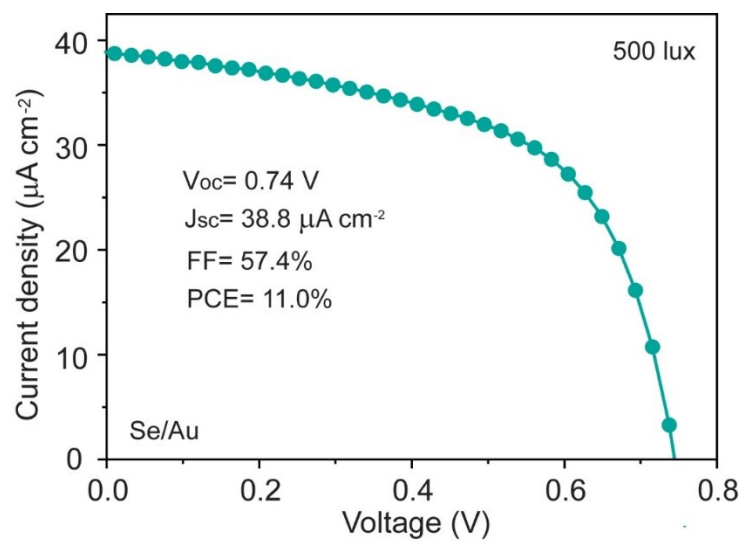


Fig. S7. J-V curve of Se/Au device under indoor illumination at 500 lux.

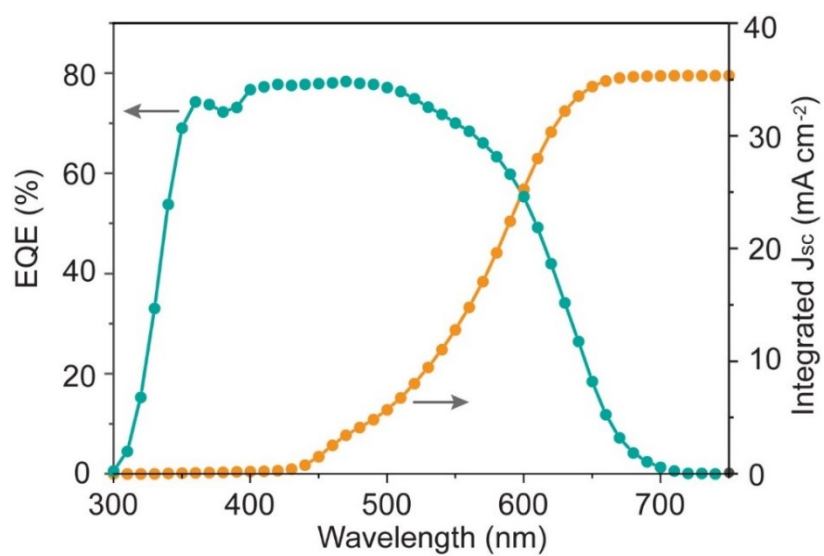


Fig. S8. EQE spectra of Se/MoO_x/Cu device and integrated current density of the device under indoor illumination at 500 lux.

Table S1. Materials cost of Se photovoltaic devices.^{4,16-19}

Component	Raw material	Price (\$/kg)	Weight (g/m ²)	Material cost (\$/m ²)
Front glass	3 mm glass (with AR)	1.25	8000	10.00
FTO	FTO	330	3.48	1.15
TiO ₂	Titanium diisopropoxide bis(acetylacetonate) (75 wt. % in isopropanol)	70	50	3.50
Se	Se	33	9.62	0.32
Au	Au	63400	1.55	98.30
Ag	Ag	798	0.84	0.67
Cu	Cu	9.6	0.72	0.007
MoO _x	MoO _x	24	0.07	0.002

Table S2. Summary of photovoltaic parameters of Se/MoO_x/Cu devices with different thicknesses of MoO_x.

Thickness	Voc (V)	Jsc (mA cm ⁻²)	FF (%)	PCE (%)
5 nm	0.84	11.0	51.7	4.8
10 nm	0.87	11.2	54.0	5.3
15 nm	0.89	11.4	53.6	5.4
20 nm	0.86	11.1	53.9	5.1
30 nm	0.85	10.9	51.8	4.8

Table S3. Summary of photovoltaic parameters of Se devices with and without a MoO_x layer of 15 nm.

devices	V _{oc} (V)	J _{sc} (mA cm ⁻²)	FF (%)	PCE (%)
Se/Au	0.89	11.5	55.0	5.6
Se/MoO _x /Au	0.90	11.9	54.1	5.8
Se/Cu	0.65	10.1	48.4	3.2
Se/MoO _x /Cu	0.89	11.4	53.6	5.4

Table S4. Materials and incident light source dependent performance of IPV devices.

Active Material	Light Source	Luminance (Lux)	PCE (%)
a-Si	LED	500	9.6 ⁵
CIGS	Halogen	500	10.2 ⁶
GaAs	LED	580	19.4 ⁷
DSC	LED	1000	28.9 ⁸
CH ₃ NH ₃ PbI ₃	FL	1000	35.2 ⁹
(CsFAMA)Pb(I _{1-x} Br _x) ₃	LED	1000	40.2 ¹⁰
Cs ₃ Sb ₂ I ₉	LED	1000	9.2 ¹¹
Cs ₃ Sb ₂ Cl _x I _{9-x}	FL	1000	4.9 ¹²
TPD-3F-51K:IT-4F	FL	1000	21.8 ¹³
P3HT:ICBA	LED	500	13.4 ¹⁴
BDT-2T-ID:PNP	LED	200	16.0 ¹⁵
Se(Au)	LED	500	11.0
Se(Cu)	LED	500	10.4

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